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Attorney's Docket No. 5308-157IP2

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.

Confirmation No.: 3570

Serial No.: 10/045,542

Group Art Unit: 1762

Filed: October 26, 2001

Examiner: Michael. E. Barr

For: METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON
CARBIDE LAYER UTILIZING AN ANNEAL IN A HYDROGEN
ENVIRONMENT

Date: February 04, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37

C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

No fee is believed due; however, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50 -0220.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

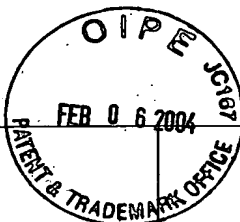
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Ban Younan



FORM PTO-1449 U.S. Department of Commerce
Patent and Trademark Office

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LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants: Das et al.

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U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1	Williams et al., "Passivation of the 4-H SiC/SiO ₂ Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.

EXAMINER
*EXAMINER

DATE CONSIDERED

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.